

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A hot plate for a semiconductor producing/examining device, comprising a resistance heating element formed on a surface of a ceramic substrate or inside the ceramic substrate,

wherein [[the]] glossiness of [[the]] a heating face of said ceramic substrate is 1.5% or more.

2. (Original) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate contains 0.5 to 10 weight % of oxygen.

3. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is subjected to an annealing treatment.

4. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

5. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 2,

wherein said ceramic substrate is subjected to an annealing treatment.

6. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 2,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

7. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 3,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

8. (Previously Presented) The hot plate for a semiconductor producing/examining device according to claim 5,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

9. (New) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate has a diameter of 200 mm or more.

10. (New) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate is a non-oxide type ceramic.

11. (New) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein said ceramic substrate contains a sintering aid.

12. (New) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein a silicon wafer is distanced from said ceramic substrate and heated.

13. (New) The hot plate for a semiconductor producing/examining device according to claim 1,

wherein the glossiness of the heating face of said ceramic substrate is 2.8% to 165%.

14. (New) A hot plate comprising:

a ceramic substrate having a heating face which is configured to face a work to be heated, the heating face having glossiness of at least 1.5% ; and

a resistance heating element provided on or in the ceramic substrate.